



Z0109NA0

4Q Triac

23 August 2013

Product data sheet

1. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Triggering in all four quadrants

2. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

3. Quick reference data

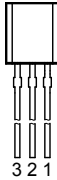
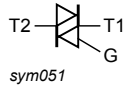
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{J}(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	12.5	A
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 45\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G+; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$; Fig. 7	0.4	-	10	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G-; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$; Fig. 7	0.4	-	10	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G-; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$; Fig. 7	0.4	-	10	mA
		$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2- G+; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$; Fig. 7	0.4	-	10	mA



4. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	 TO-92 (SOT54)	 sym051
2	G	gate		
3	T1	main terminal 1		

5. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0109NA0	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

6. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage			-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 45\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3		-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5		-	12.5	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$		-	13.8	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; SIN		-	0.78	A^2s
di_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 1\text{ A}$; $I_{\text{G}} = 20\text{ mA}$; $dI_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$; T2+ G+		-	50	$\text{A}/\mu\text{s}$
		$I_{\text{T}} = 1\text{ A}$; $I_{\text{G}} = 20\text{ mA}$; $dI_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$; T2+ G-		-	50	$\text{A}/\mu\text{s}$
		$I_{\text{T}} = 1\text{ A}$; $I_{\text{G}} = 20\text{ mA}$; $dI_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$; T2- G-		-	50	$\text{A}/\mu\text{s}$
		$I_{\text{T}} = 1\text{ A}$; $I_{\text{G}} = 20\text{ mA}$; $dI_{\text{G}}/dt = 100\text{ mA}/\mu\text{s}$; T2- G+		-	20	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current			-	1	A
P_{GM}	peak gate power			-	2	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period		-	0.1	W
T_{stg}	storage temperature			-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature			-	125	$^{\circ}\text{C}$

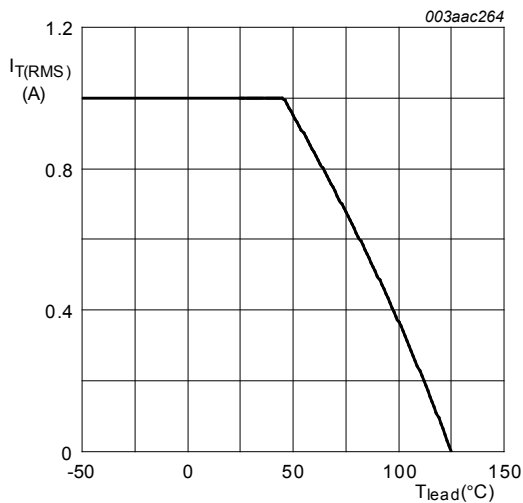
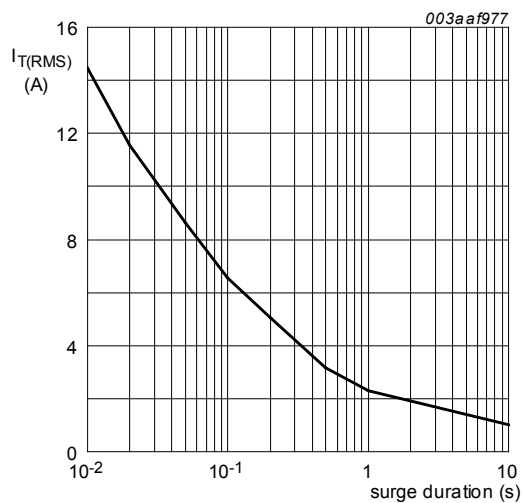


Fig. 1. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 45 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

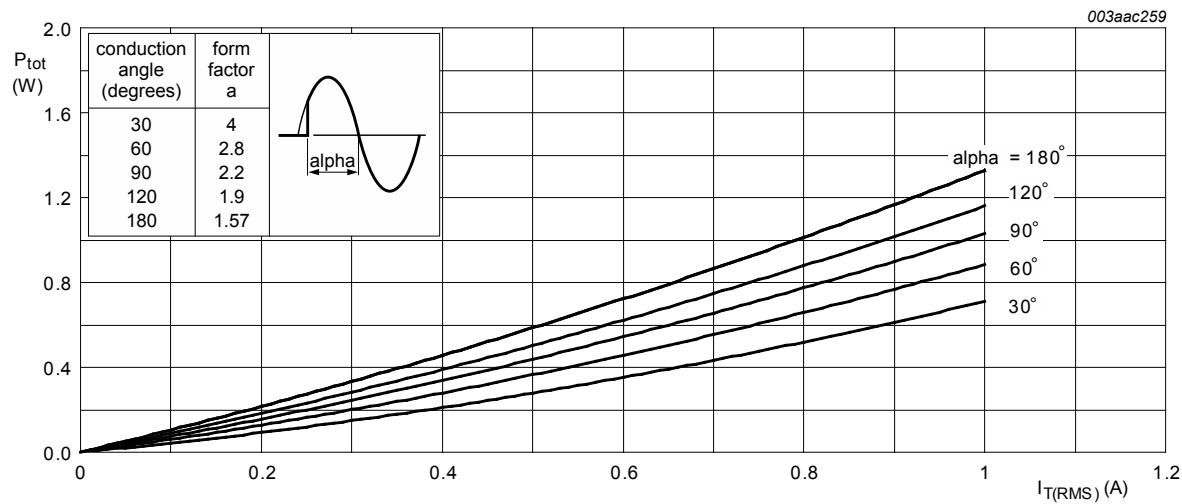


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

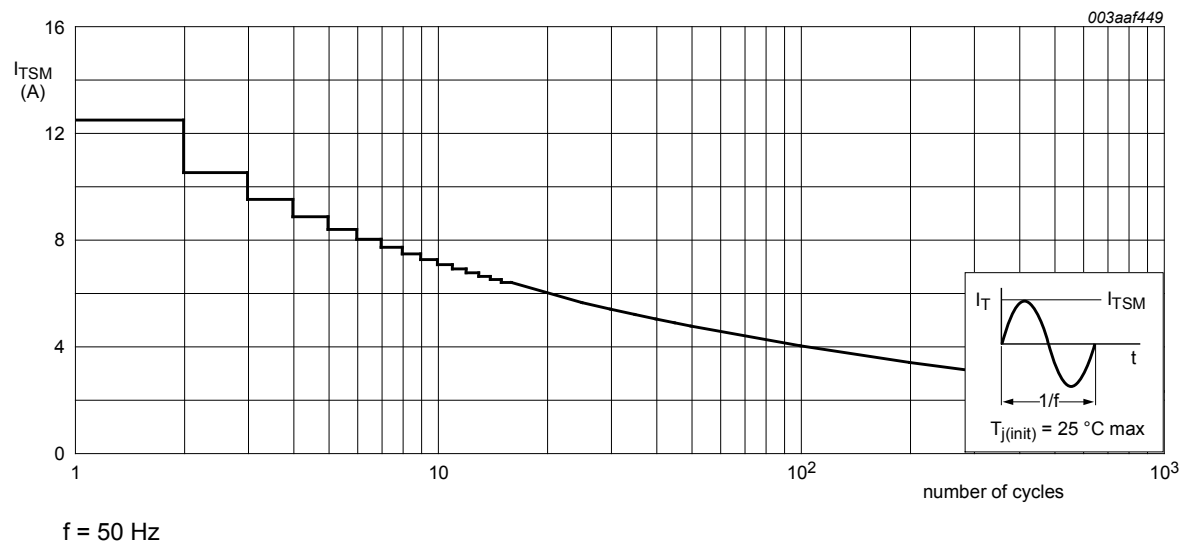


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

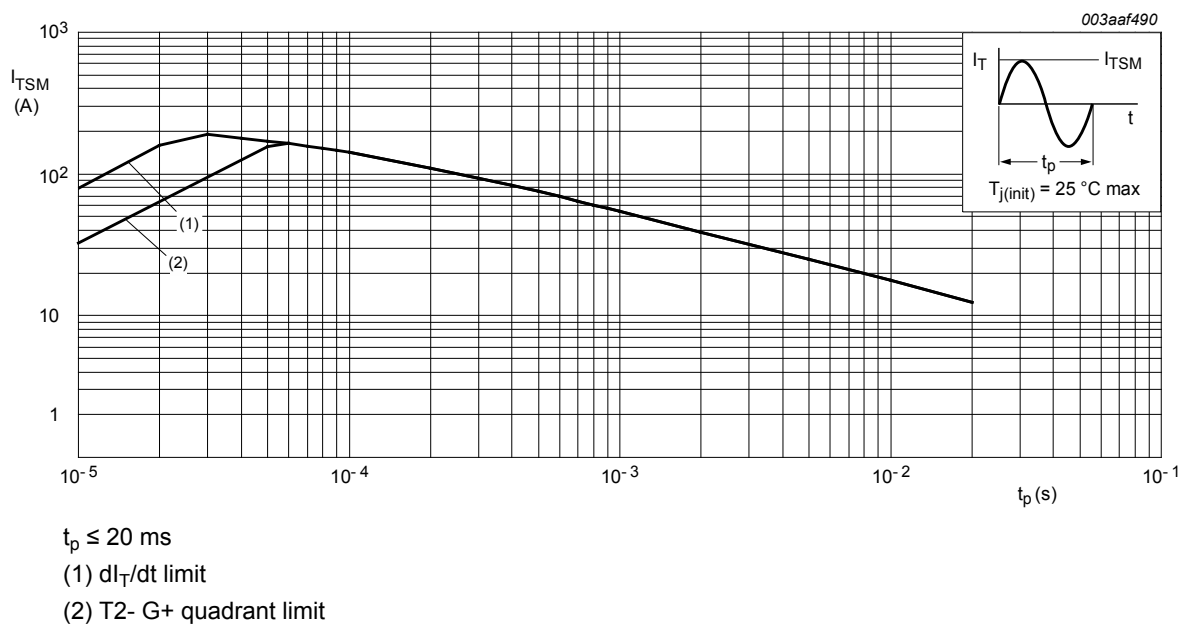


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

7. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6		-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	full cycle; printed-circuit board mounted; lead length 4 mm		-	150	-	K/W

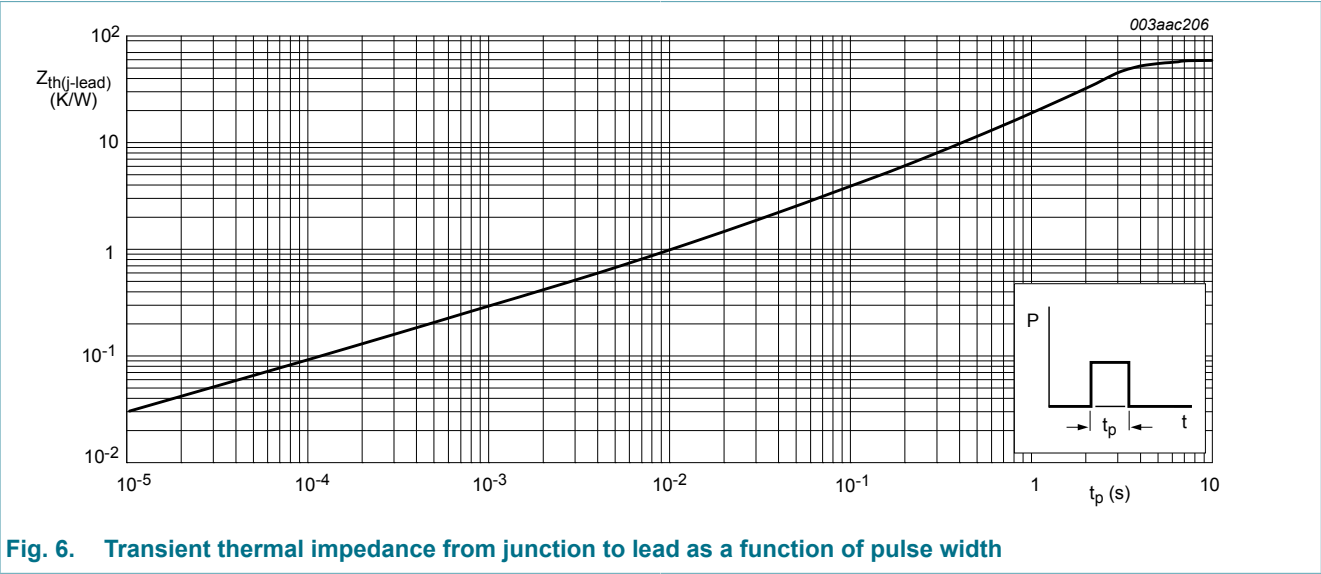
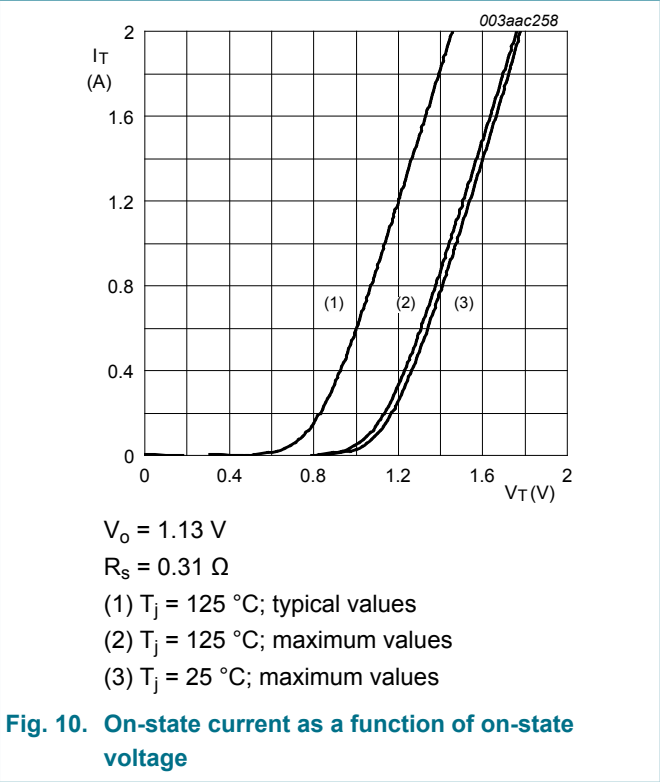
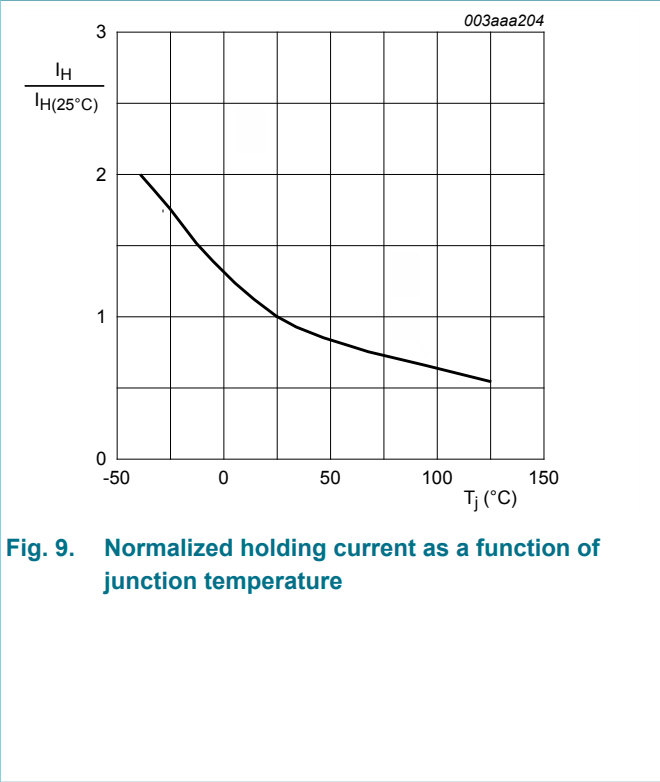
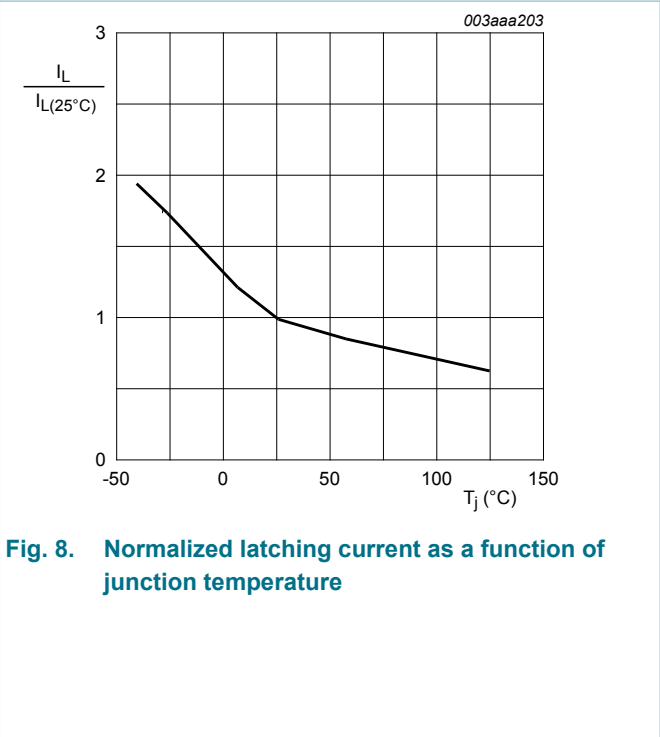
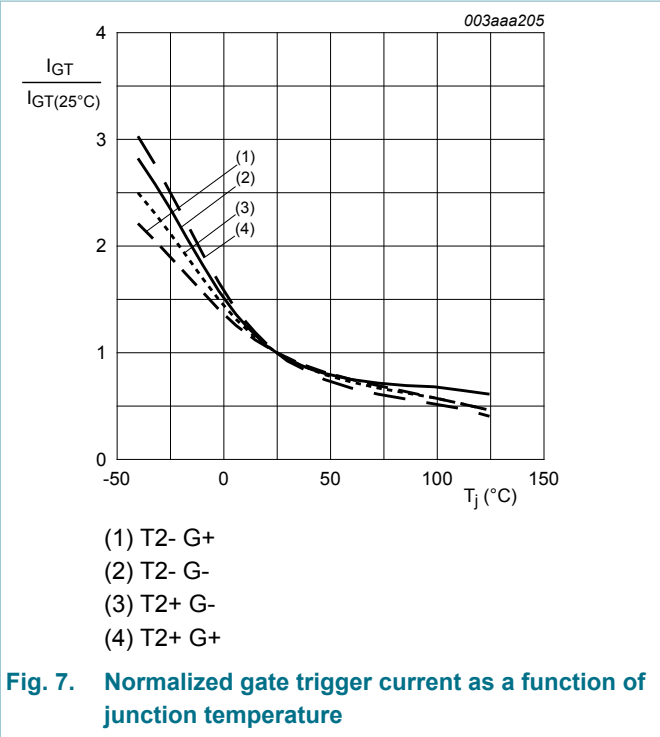


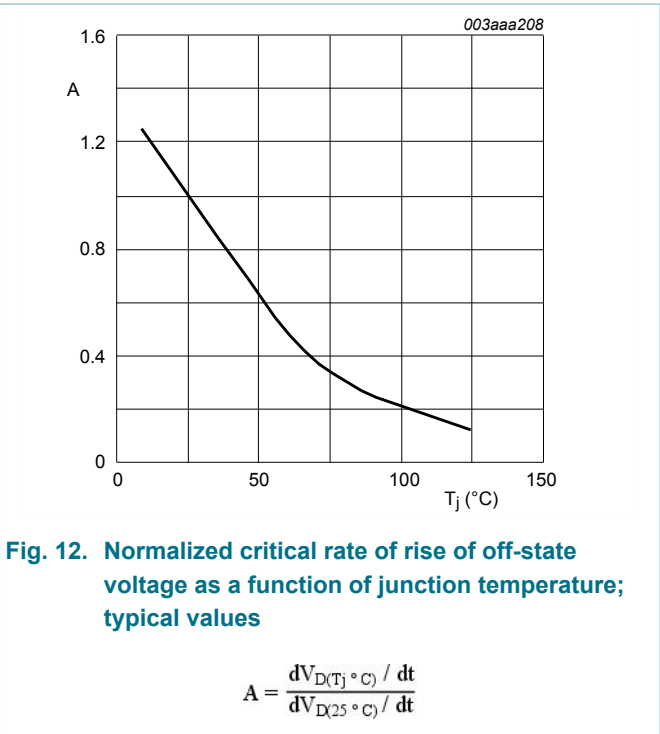
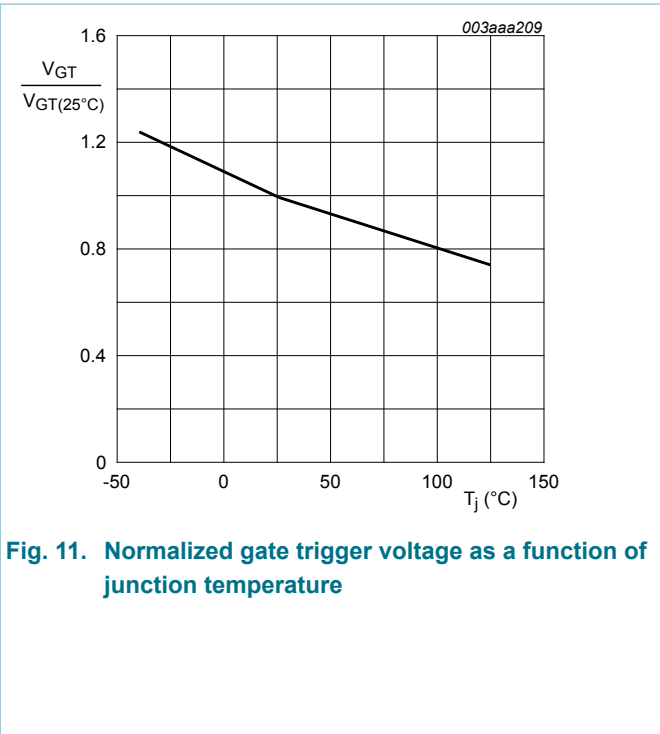
Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

8. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.4	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.4	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.4	-	10	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.4	-	10	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	15	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	30	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	15	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	15	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	-	10	mA
V_T	on-state voltage	$I_T = 1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	-	1	V
		$V_D = 800\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 11	0.2	-	-	V
I_D	off-state current	$V_D = 800\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	-	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$; $T_j = 110\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	120	-	-	V/ μs
dV_{com}/dt	rate of change of commutating voltage	$V_D = 400\text{ V}$; $T_j = 110\text{ }^\circ\text{C}$; $dI_{com}/dt = 0.44\text{ A/ms}$; gate open circuit	2	-	-	V/ μs





9. Package outline

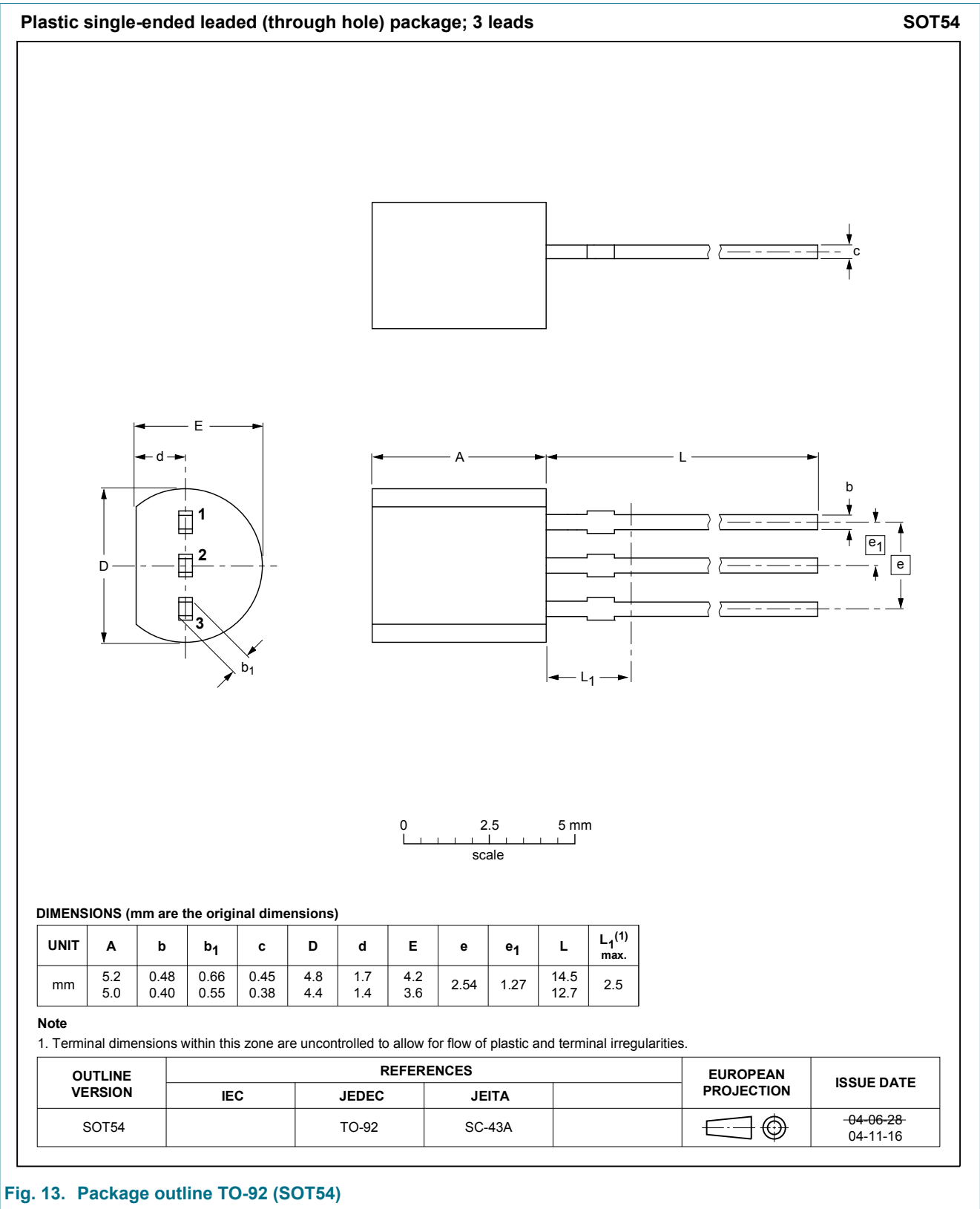


Fig. 13. Package outline TO-92 (SOT54)

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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